Date Created : 2009/04/03 Date Issued On : 2009/04/14

PCN# : **Q2091404**

DESIGN/PROCESS CHANGE NOTIFICATION -- FINAL

This is to inform you that a design and/or process change will be made to the following product(s). This notification is for your information and concurrence.

If you require data or samples to qualify this change, please contact **Fairchild Semiconductor** within 30 days of receipt of this notification.

Updated process quality documentation, such as FMEAs and Control Plans, are available for viewing upon request.

If you have any questions concerning this change, please contact:

<u>Technical Contact:</u>

Name: Rivero, Douglas

E-mail: Doug.Rivero@notes.fairchildsemi.com

Phone: 1-408-822-2143

PCN Originator:

Name: Kalabkova, Ivana

E-mail: Ivana.Kalabkova@notes.fairchildsemi.com

Phone: 408-822-2187

Implementation of change:

Expected 1st Device Shipment Date: 2009/07/13

Earliest Year/Work Week of Changed Product: 0929

Change Type Description: Assembly Process, Lead Finish Composition, Package Change (Lead Frame), Package External Dimension

Description of Change (From): Selected MOSFET products assembled in Power 56 package, in which the current Die Attach Pad & Leadpost plating is NiPdAu; current Gate Leadpost Plating is NiPdAu; current Gate Interconnect is 5mil Al wire; current Singulation Method is Saw-Singulation and current Plating Finish is NiPdAu. To view "From/To" Dimensional Outline, please refer to the attached table "Dimensional Outline."

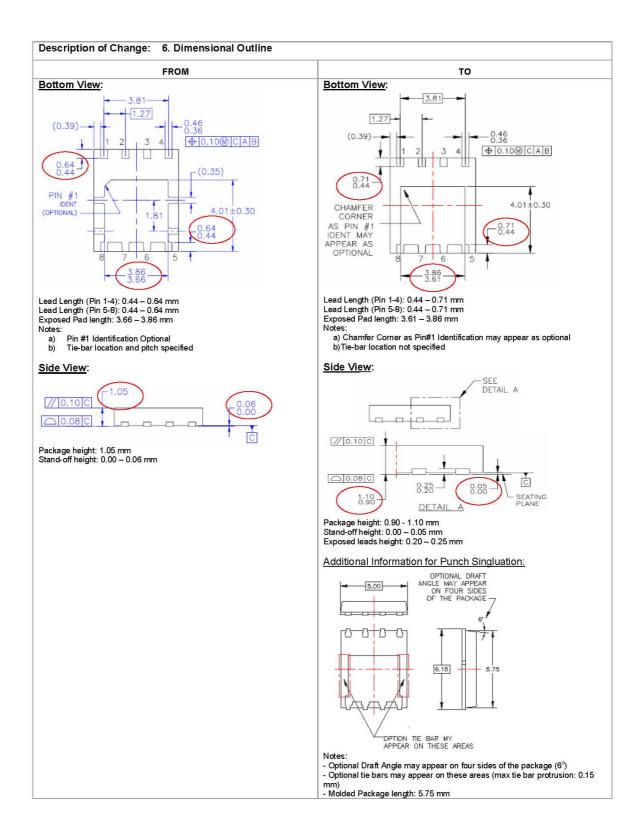
Description of Change (To): The alternate Die Attach Pad & Leadpost plating will be Bare Cu; alternate Gate Leadpost Plating will be Ag; alternate Gate Interconnect will be 2mil Cu wire; alternate Singulation Method will be Punch-singulation and the alternate Plating Finish will be Pure Sn.

Reason for Change: In addition to the current qualified Saw-singulated Power 56 package, Fairchild Semiconductor intends to qualify the Punch-singulated Power 56 to support volume ramp. There will be no change to the part number as the Punch and Saw-singulated Power 56 share common land pattern dimensions and are interchangeable

Change From

Description of Change:	FROM:	TO:
Die Attach Pad & Source Leadpost plating	NiPdAu	Bare Cu
Gate Leadpost Plating	NiPdAu	Ag
Gate Interconnect	5mil Al wire	2mil Cu wire
Singulation Method	Saw Singulation	Punch Singulation
5. Plating Finish	NiPdAu	Pure Sn

Change To



Qual/REL Plan Numbers: Q20090181

Qualification:

This change will not affect the devices' specifications or functional performance. Product quality, reliability and MSL performance will be maintained. There will be no change to the part number as both the Punch and Saw-singulated Power 56 share common land pattern dimensions

and are interchangeable. The reliability qualification is complete and results are detailed in the attached table:

Results/Discussion for Qual Plan NumberQ20090181

Test: (Board Level Tem	perature Cycle) C	onditions: -	10C, 10	0C Standa	rd: IPC-9701	L	
	Device	100-HOU		500-HOURS	1000		Failure Code
Q20090181AABTMCL	FDMS8692	0/77					
				0/77			
					0/77		
Q20090181BABTMCL F	FDMS8672AS	0/77			0, , ,		
Q20090101B/1B/1MCE	DIVIDUOT ZI ID	0, , ,		0/77			
				0,7,7	0/77		
Q20090181CABTMCL F	FDMS8670AS	0/77			0///		
Q20090181CAB1MCL 1	DMS6070AS	0/ / /		0/77			
				0/77	0.77		
					0/77		
Test: (High Temperature	e Reverse Bias) C	onditions: 1	125C, 24	V Standa	d: JESD22-A	A108	
Lot	Device		168-HOU		500-HOURS		Failure Code
Q20090181BAHTRB	FDMS8672AS		0/77		500 110 0115		Tanare Code
Q20090181BAHTRB	FDMS8672AS		0, 1 1		0/77		
Q20090181CAHTRB	FDMS8670AS			0/77			
Q20090181CAHTRB	FDMS8670AS		0/ / /				
Q20090181CAH1KB	TDMS8070AS				0/77		
Test: (High Temperature	e Reverse Bias) C	onditions: 1	$175C, 2\overline{4}$	V Standar	rd: JESD22-A	A108	
Lot	Device		168-HOU	JRS	500-HOURS		Failure Code
Q20090181AAHTRB	FDMS8692		0/77				
Q20090181AAHTRB	FDMS8692				0/77		
Toots (III-1-T-	Storage I:C \ I C	aditi 1	750 10	andani IEC	D22 A 102		1
Test: (High Temperature		onattions: 1	/3C St		D22-A103		
Lot	Device			500-HOURS		Fai	lure Code
Q20090181AAHTSL	FDMS8692			0/77			
Q20090181BAHTSL	FDMS8672AS	1		0/77			
Q20090181CAHTSL	FDMS8670AS	}		0/77			
Test: (Highly Accelerate	ed Stress Test) Co	nditions: 84	5%RH 1	130C 24V	Standard: II	SD22	-A110
		narrions. oc	70111,		Standard. 31		
Lot	Device					Fai	lure Code
Q20090181AAHAST1		FDMS8692		0/77			
Q20090181BAHAST1		FDMS8672AS		0/77			
Q20090181CAHAST1	FDMS8670AS	l		0/77			
Test: (Power Cycle) Co	onditions: Delta 10	0C, 2 Min c	cycle Si	tandard: M	L-STD-750-	1036	
Lot	Device		5000-CY		10000-CYCLE		Failure Code
Q20090181AAPRCL	FDMS8692		0/77	CLLS	TOOGO CTCEE		ranare code
Q20090181AAPRCL	FDMS8692			0/77			
Q20090181AA1 RCL Q20090181BAPRCL				0/77			
`		FDMS8672AS 0/77		0/22			
Q20090181BAPRCL		MS8672AS			0/77		
Q20090181CAPRCL	FDMS8670AS		0/77		0.177		
Q20090181CAPRCL	FDMS8670AS				0/77		
Test: (Precondition) Co	onditions: Standar	d: JESD22-	A113		·		
Lot	Device			Results		Fai	lure Code
Q20090181AAPCNL1A	FDMS8692			0/231			
Q20090181BAPCNL1A				0/231		+	
Q20090181CAPCNL1A	FDMS8670AS			0/231			
Test: (Temperature Cycl	le) Conditions: -6	5C, <u>15</u> 0C 3			A104		
Lot	Device		100-CYC	CLES	500-CYCLES		Failure Code
Q20090181AATMCL1	FDMS8692		0/77				
Q20090181AATMCL1	FDMS8692				0/77		
Q20090181BATMCL1	FDMS8672AS		0/77				
Q20090181BATMCL1	FDMS8672AS			0/77			
Q20090181CATMCL1	FDMS8670AS						
Q20090181CATMCL1	FDMS8670AS			0/77			
	1	DII 1000'	G. 1	1 IECD 22			I
Test: (Unbiased HAST)	Conditions: 85%]	KH, 130C	Standar		A118		
Lot	Device			96-HOURS		Fai	lure Code
Q20090181AAUHAST1	FDMS8692	0,		0/77			
Q20090181BAUHAST1				0/77		İ	
Q20090181CAUHAST1 FDMS8670AS				0/77			

Product Id Description: Fairchild Semiconductor's selected MOSFET devices assembled in

Power 56 package will be affected by this change. Please refer to the Affected FSIDs section.

Affected FSIDs:

FDMS3500	FDMS3662	FDMS5352
FDMS6673BZ	FDMS6681Z	FDMS7660
FDMS7670	FDMS7672	FDMS8460
FDMS86101	FDMS8660AS	FDMS8662
FDMS8670	FDMS8670AS	FDMS8670S
FDMS8670S_SB82233	FDMS8672AS	FDMS8672S
FDMS8674	FDMS8680	FDMS8692
FDMS8848NZ	FDMS8880	